

CORRIGENDUM

Corrigendum: On-chip light sources for silicon photonics

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In the version of this article originally published, the substrate used in reference 111 to grow InAs/GaAs quantum dots was silicon. However, the authors have found out that 500 nm of germanium was first grown on silicon by chemical vapor deposition before growing InAs/GaAs quantum dots. Therefore, the InAs/GaAs quantum dots reported in reference 111 are actually grown on Ge-on-Si substrate. Therefore,

1. In Table 2, the substrate of reference 111 should be ‘Ge-on-Si’ instead of ‘Si’.
2. In ‘III–V-BASED SI LASER’ section, ‘Another method to suppress TDs is using nano-structures, notably QDs¹⁰³⁻¹¹⁰’ should be ‘Another method to suppress TDs is using nano-structures, notably QDs¹⁰³⁻¹¹¹’.
3. In ‘III–V-BASED SI LASER’ section, ‘Electrically pumped 1.3- μm InAs/GaAs QD lasers monolithically grown on Ge¹⁰⁵, Ge-on-Si¹⁰⁶, and Si¹⁰⁷⁻¹¹¹’ should be ‘Electrically pumped 1.3- μm InAs/GaAs QD lasers monolithically grown on Ge¹⁰⁵, Ge-on-Si^{106,111}, and Si¹⁰⁷⁻¹¹⁰’.

We apologize for any inconvenience this may have caused.